

Claims:

1. An electrode for dry etching a wafer, said electrode comprising a first electrode and a second electrode for removing foreign materials from the edge of the wafer by plasma, said first electrode including a first flat plate and a ring-shaped first protrusion corresponding to one surface of the edge of a wafer, and said second electrode including a second flat plate and a ring-shaped second protrusion corresponding to the other surface of the edge of the wafer, wherein said first protrusion and said second protrusion are the same size.

2.(amended) The electrode for dry etching a wafer as set forth in claim 1, wherein an insulation layer is deposited on or an insulating material is attached to an inner area of the upper surface of the first electrode, which is inside of the first protrusion.